**MRF5583** 

 $I_C = -500 \text{ mA}$ 

SURFACE MOUNT HIGH-FREQUENCY

**TRANSISTOR** 

**PNP SILICON** 

**CASE 751-05, STYLE 1** 

(SO-8)

# The RF Line PNP Silicon High-Frequency Transistor

... designed for amplifier, oscillator or frequency multiplier applications in industrial equipment. Suitable for use as a Class A, B or C output driver or pre-driver stages in VHF and UHF.

- Low Cost SORF Plastic Surface Mount Package
- Guaranteed RF Specification |S<sub>21</sub>|<sup>2</sup>
- S-Parameter Characterization
- Tape and Reel Packaging Options Available by adding suffix:

R1 suffix = 500 units per reel

R2 suffix = 2,500 units per reel

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	-30	V
Collector-Base Voltage	V <sub>СВО</sub>	-30	V
Emitter–Base Voltage	VEBO	-3.0	V
Collector Current — Continuous	IC	-500	mA
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

# **DEVICE MARKING**

MRF5583 = 5583

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	1.0 8.0	Watt mW/°C
Storage Temperature	T <sub>stg</sub>	150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V(BR)CEO	-30	_	_	V		
Collector–Base Breakdown Voltage (I <sub>C</sub> = -10 μA)	V(BR)CBO	-30	_	_	V		
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –100 μA)	V(BR)EBO	-3	_	_	V		
Collector Cutoff Current (V <sub>CB</sub> = −20 V)	ICBO	_	_	-1.0	μΑ		
Emitter Cutoff Current (V <sub>EB</sub> = -2.0 V)	I <sub>EBO</sub>	_	_	-0.5	μΑ		
ON CHARACTERISTICS							
DC Current Gain (I <sub>C</sub> = $-40$ mA, V <sub>CE</sub> = $-2.0$ V) (I <sub>C</sub> = $-100$ mA, V <sub>CE</sub> = $-2.0$ V) (I <sub>C</sub> = $-300$ mA, V <sub>CE</sub> = $-5.0$ V)	hFE	20 25 15	_ _ _	100 —	_		
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -100 mA, I <sub>B</sub> = -10 mA)	V <sub>CE(sat)</sub>	_	_	0.8	V		
Base–Emitter On Voltage (I <sub>C</sub> = -100 mA, V <sub>CE</sub> = -2.0 V)	V <sub>BE(on)</sub>	_	_	1.8	V		
SMALL-SIGNAL CHARACTERISTICS							
Current-Gain — Bandwidth Product	fΤ	_	2100	_	MHz		

# REV 6



12.5

 $|S_{21}|^2$ 

15.5

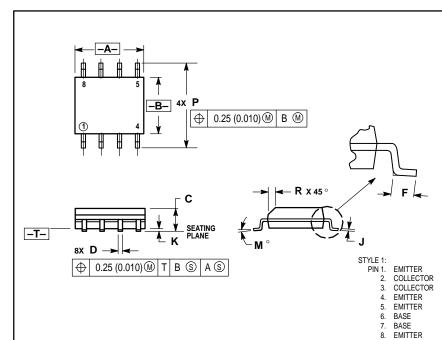
 $(I_C = -35 \text{ mA}, V_{CE} = -15 \text{ V}, f = 100 \text{ MHz})$ 

Insertion Gain ( $V_{CE} = -15 \text{ V}$ ,  $I_{C} = -35 \text{ mA}$ , f = 250 MHz)

V <sub>CE</sub> I <sub>C</sub> f		s <sub>11</sub>		s <sub>21</sub>		s <sub>12</sub>		S <sub>22</sub>		
(Volts)	(mA)	(MHz)	S <sub>11</sub>	ф	S <sub>21</sub>	ф	S <sub>12</sub>	ф	S <sub>22</sub>	ф
-15	-35	10	0.47	-57	64.7	155	0.01	60	0.83	-26
		30	0.59	-116	42.2	126	0.02	44	0.56	-58
		50	0.63	-140	28.8	113	0.02	39	0.39	-74
		70	0.64	-151	21.4	105	0.02	42	0.30	-82
		100	0.65	-161	15.4	97	0.02	45	0.24	-80
		300	0.67	179	5.23	79	0.05	58	0.13	-109
		500	0.67	168	3.11	66	0.07	60	0.20	-114
		700	0.67	160	2.24	57	0.09	60	0.24	-116
		1000	0.66	146	1.54	44	0.13	60	0.30	-123

**Table 1. Common Emitter S-Parameters** 

# **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.18	0.25	0.007	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

**CASE 751-05 ISSUE M** 

MOTOROLA RF DEVICE DATA MRF5583

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